

**In the Claims**

Claims 1-5 (canceled).

Claim 6 (currently amended): The method of claim 4 An atomic layer deposition method comprising:

utilization of an electric field gradient within an atomic layer deposition reaction chamber to align molecules during the atomic layer deposition as at least portions of the molecules are incorporated into a material formed over a semiconductor substrate; and

wherein:

the molecules are first molecules;

the atomic layer deposition process comprises provision of second molecules into the atomic layer deposition reaction chamber at a substantially non-overlapping time relative to the first molecules and incorporation of at least portions of the second molecules into the material formed over the semiconductor substrate; and

the electric field gradient is removed from within the atomic layer deposition reaction chamber prior to incorporating at least portions of the second molecules into the material.

Claim 7 (original): The method of claim 6 wherein the first molecules are ammonia and the second molecules are SiCl<sub>4</sub>.

Claim 8 (canceled).

Claim 9 (currently amended): ~~The method of claim 4~~ An atomic layer deposition method comprising:

utilization of an electric field gradient within an atomic layer deposition reaction chamber to align molecules during the atomic layer deposition as at least portions of the molecules are incorporated into a material formed over a semiconductor substrate; and

wherein:

the molecules are first molecules;

the atomic layer deposition process comprises provision of second molecules into the atomic layer deposition reaction chamber at a substantially non-overlapping time relative to the first molecules and incorporation of at least portions of the second molecules into the material formed over the semiconductor substrate;

the electric field gradient is in a first configuration during the incorporation of at least portions of the first molecules into the material and is in a second configuration, different from the first configuration, during the incorporation of at least portions of the second molecules into the material.

Claim 10 (currently amended): The method of claim 4 An atomic layer deposition method comprising:

utilization of an electric field gradient within an atomic layer deposition reaction chamber to align molecules during the atomic layer deposition as at least portions of the molecules are incorporated into a material formed over a semiconductor substrate; and

wherein:

the molecules are first molecules;

the electric field gradient is in a first configuration during the incorporation of at least portions of the first molecules into the material;

the first configuration of the electric field gradient comprises an increase of the electric field along a first vector within the atomic layer deposition chamber during the alignment of the first molecules;

the atomic layer deposition process comprises provision of second molecules into the atomic layer deposition reaction chamber at a substantially non-overlapping time relative to the first molecules and incorporation of at least portions of the second molecules into the material formed over the semiconductor substrate;

after the incorporation of at least portions of the first molecules into the material, the electric field gradient is changed to a second configuration in which the electric field increases along a second vector different from the first vector; and

the electric field gradient remains in the second configuration during the incorporation of at least portions of the second molecules into the material.

**Claim 11 (original):** The method of claim 10 wherein an angular difference between the first and second vectors is about 180 degrees.

**Claims 12 -34 (canceled).**